

Abstract

A semiconductor device including: a plurality of fin-shaped patterns spaced apart from each other in a first direction and extending in a second direction on a substrate; a field insulating layer covering sidewalls of the plurality of fin-shaped patterns and disposed between the fin-shaped patterns; a source/drain pattern connected to the plurality of fin-shaped patterns on the field insulating layer, the source/drain pattern including bottom surfaces respectively connected to the fin-shaped patterns, and at least one connection surface connecting the bottom surfaces to each other; and a sealing insulating pattern extending along the connection surface of the source/drain pattern and an upper surface of the field insulating layer, wherein the source/drain pattern includes a silicon-germanium pattern doped with a p-type impurity.

FIG. 2